

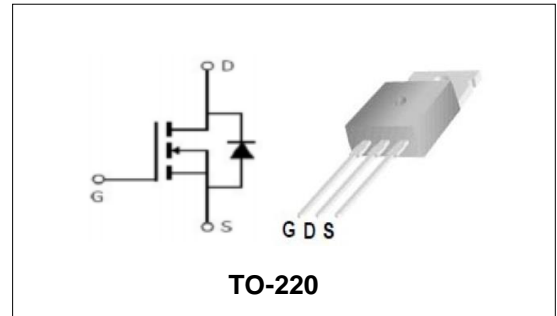
**40V/160A N-Channel Advanced Power MOSFET****Features**

- Fast switching capability
- Robust design with better EAS performance
- EMI Improved

BVDSS	40	V
ID	160	A
RDSON@VGS=10V	1.8	mΩ
RDSON@VGS=4.5V	2.7	mΩ

**Applications**

- Server/Telecom
- High Power Supply
- E-Tools
- Motor Driver
- BMS

**TO-220****Order Information**

Product	Package	Marking	Tube	Carton
PGP04N015	TO-220	PGP04N015	50PCS	5000PCS

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>				
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	40	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
T <sub>J</sub>	Maximum Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
I <sub>S</sub>	Diode Continuous Forward Current	TC =25°C	150	A
<b>Mounted on Large Heat Sink</b>				
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note1)	130	mJ	
I <sub>DM</sub>	Pulse Drain Current Tested (Silicon Limit) (Note2)	TC =25°C	480	A
I <sub>D</sub>	Continuous Drain current	TC =25°C	160	A
P <sub>D</sub>	Maximum Power Dissipation	TC =25°C	83	W
R <sub>θJa</sub>	Thermal Resistance Junction-to-Ambient (Note3)	65	°C/W	
R <sub>θJc</sub>	Thermal Resistance Junction-to-Case (Note3)	1.5		



## 40V/160A N-Channel Advanced Power MOSFET

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
V <sub>(BR)DSS</sub>	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain current(Tc=25°C)	VDS=32V,VGS=0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
V <sub>GS(TH)</sub>	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.0	1.8	2.5	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance (Note4)	VGS=10V, ID=30A	--	1.8	2.6	mΩ
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance (Note4)	VGS=4.5V, ID=20A	--	2.7	3.6	mΩ
<b>Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated) (Note5)</b>						
C <sub>iss</sub>	Input Capacitance	VDS=20V, VGS=0V, F=1MHz	--	3160	--	pF
C <sub>oss</sub>	Output Capacitance		--	1100	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	150	--	pF
Q <sub>g</sub>	Total Gate Charge	VDS=20V, ID=75A, VGS=10V	--	95	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	15	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	11	--	nC
<b>Switching Characteristics (Note5)</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	VDS=20V, ID=75A, RG=3.9Ω, VGS=10V	--	12.5	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	7	--	nS
t <sub>d(off)</sub>	Turn-off Delay Time		--	50	--	nS
t <sub>f</sub>	Turn-off Fall Time		--	8.5	--	nS
<b>Source- Drain Diode Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
V <sub>SD</sub>	Forward on voltage	IS=30A,VGS=0V	--	0.84	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	Tj=25°C , I <sub>SD</sub> = 140A ISD=30A, Di/dt=100A/us	--	31	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	110	--	nc

Note:

- Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25° C, R<sub>G</sub> =25Ω, VDS =20V, VGS =10V. Part not recommended for use above this value.
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.



40V/160A N-Channel Advanced Power MOSFET

Typical Performance Characteristics

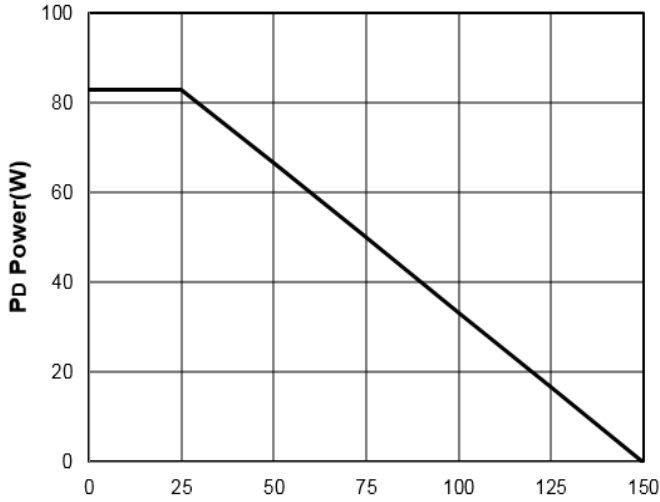


Figure1: T<sub>j</sub> Junction Temperature (°C)

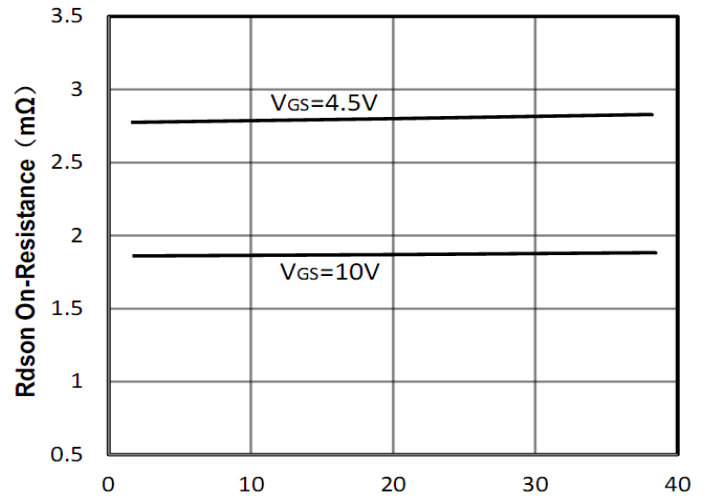


Figure2: I<sub>d</sub> Drain Current (A)

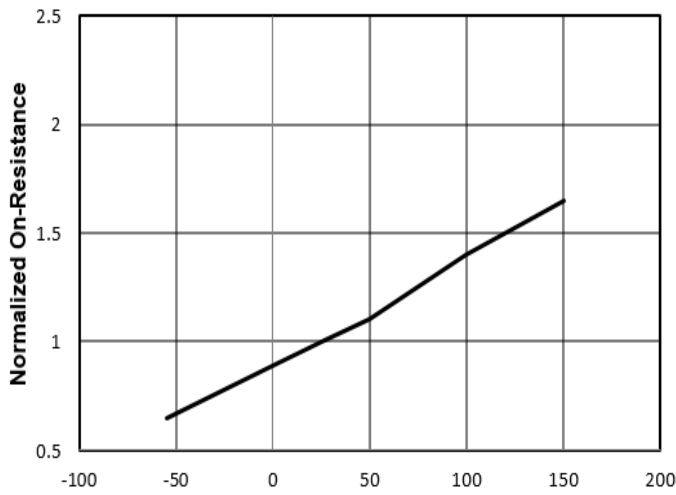


Figure3: T<sub>j</sub> Junction Temperature (°C)

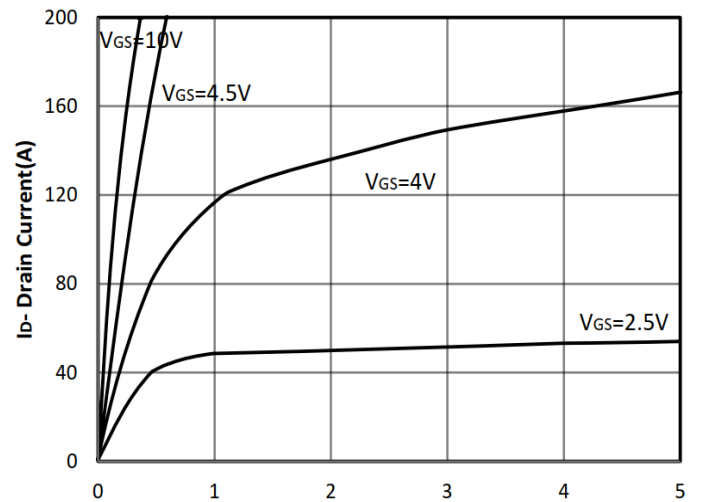


Figure4: V<sub>ds</sub> Drain-Source Voltage (V)

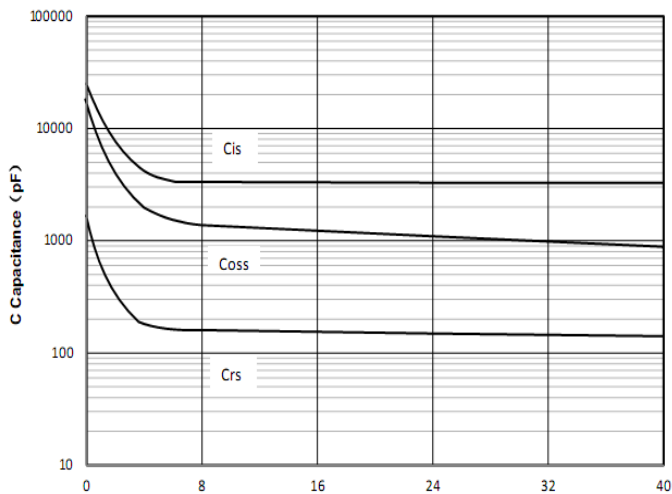


Figure5: V<sub>ds</sub> Drain-Source Voltage (V)

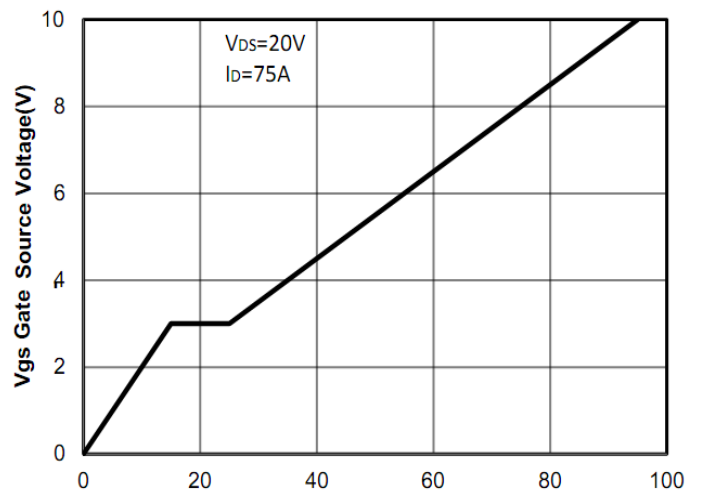


Figure6: Q<sub>g</sub> Gate Charge (nC)



40V/160A N-Channel Advanced Power MOSFET

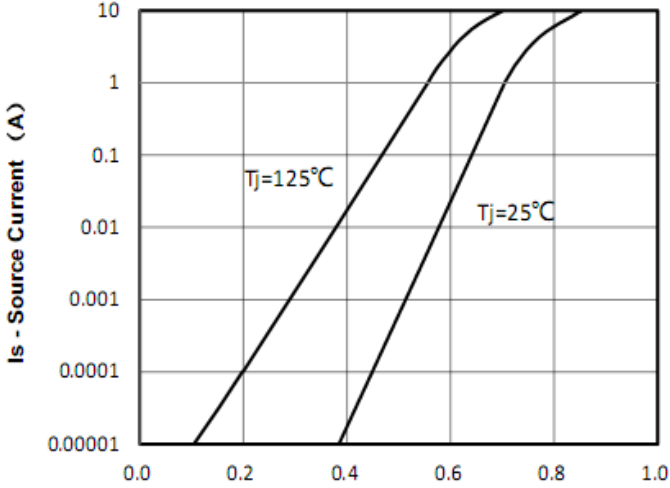


Figure7: Vsd Source-Drain Voltage (V)

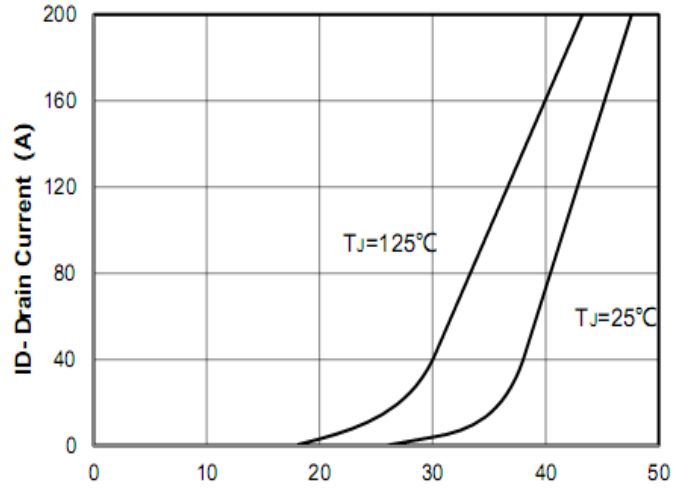


Figure8: Vgs Gate-Source Voltage (V)

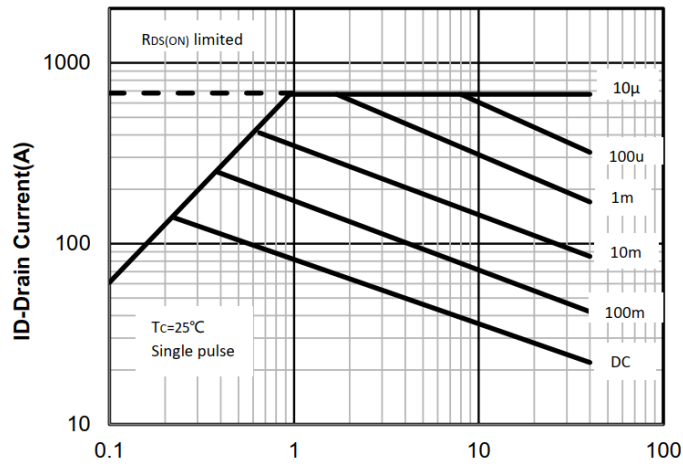


Figure9: Vsd Drain -Source Voltage (V)

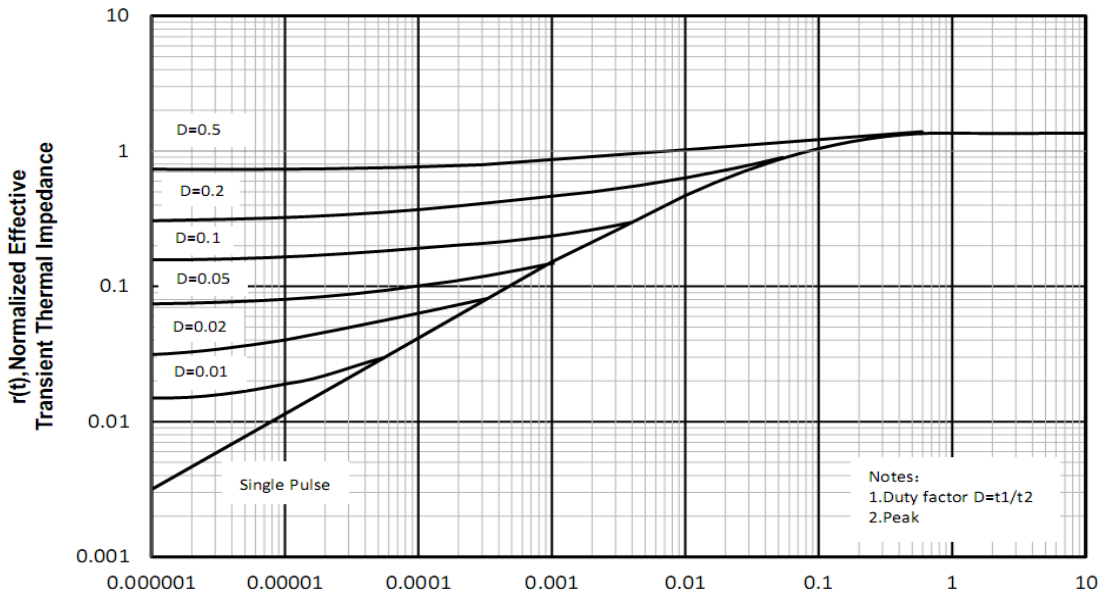
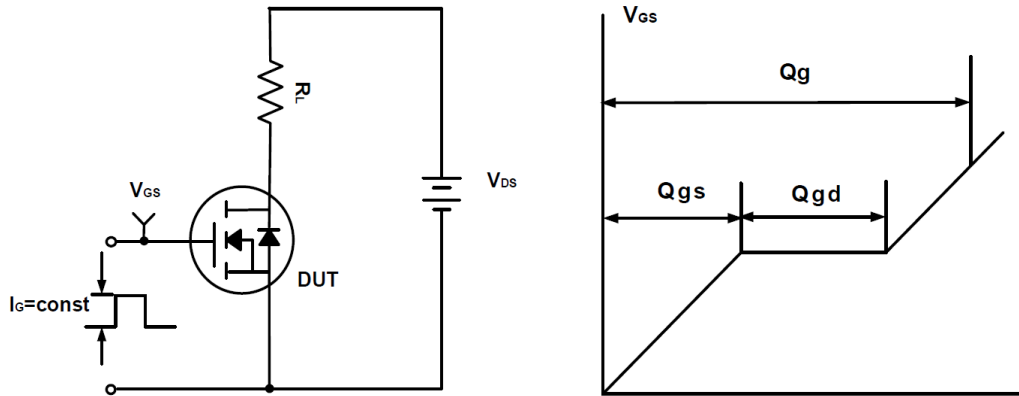
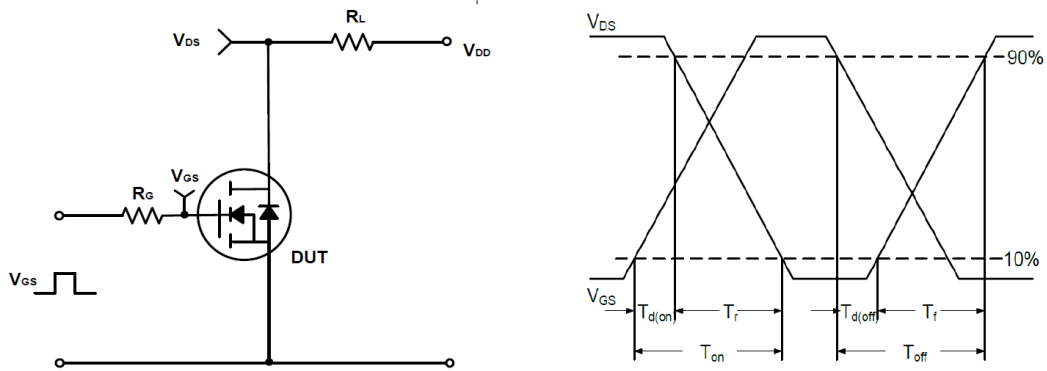
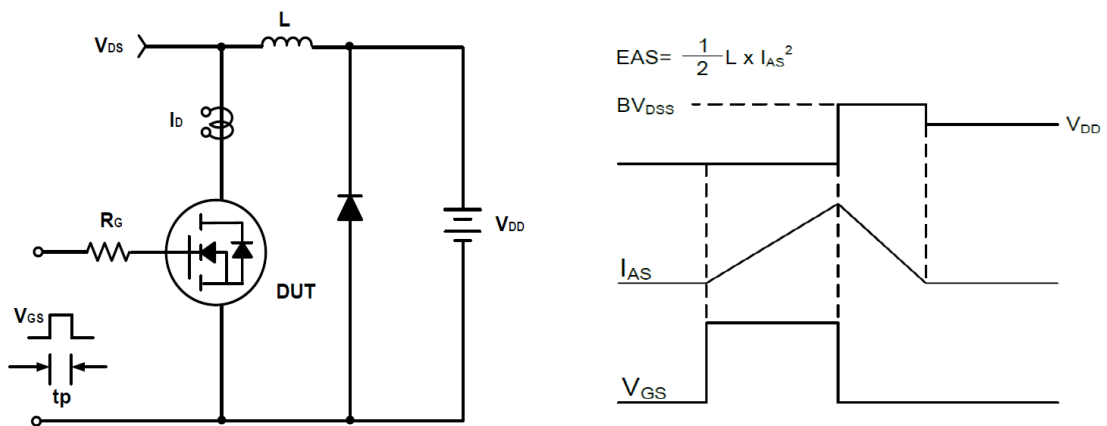
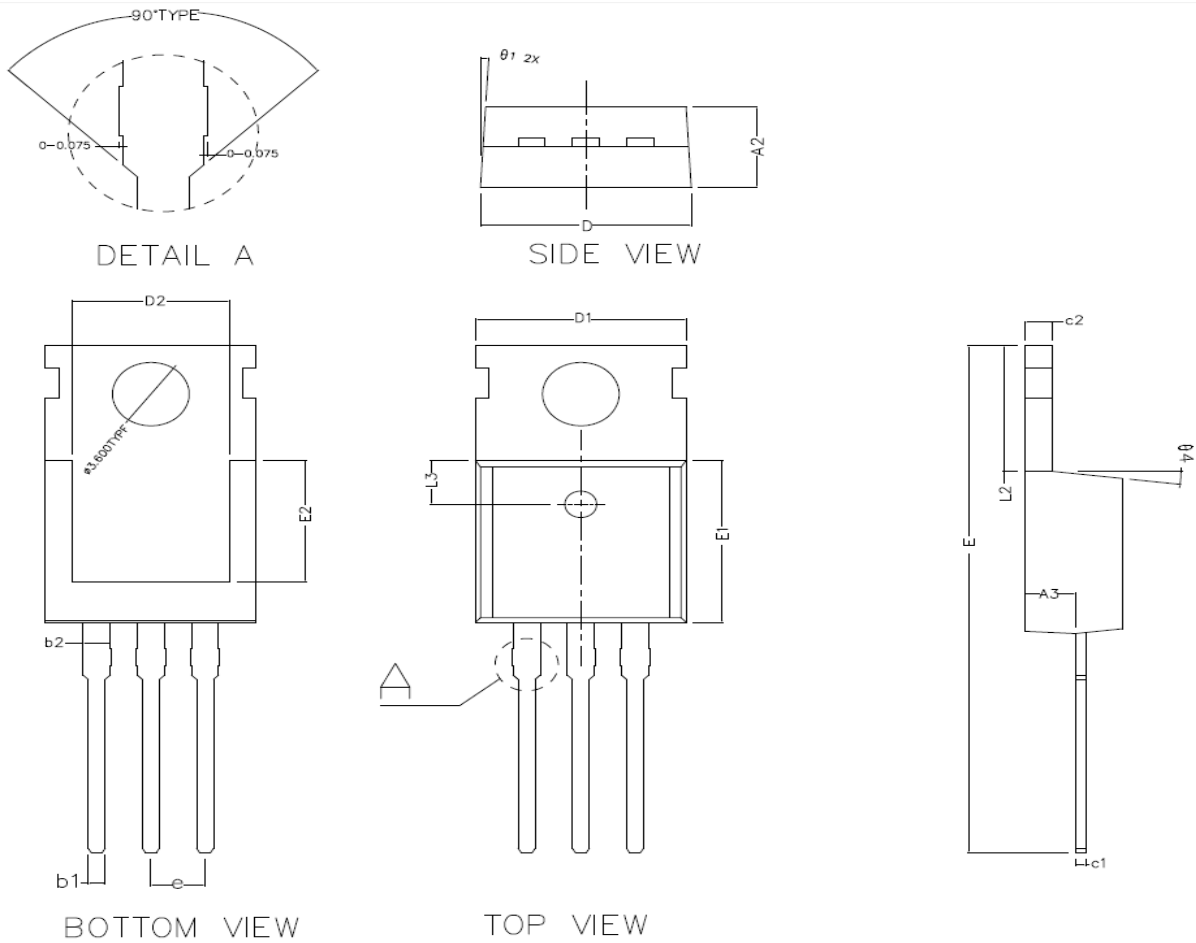


Figure10: Square Wave Pulse Duration (sec)

**40V/160A N-Channel Advanced Power MOSFET**
**Test Circuit and Waveform:**

**Figure A Gate Charge Test Circuit & Waveforms**

**Figure B Switching Test Circuit & Waveforms**

**Figure C Unclamped Inductive Switching Circuit & Waveforms**

**40V/160A N-Channel Advanced Power MOSFET**
**TO-220 Package Outline Dimensions (Units: mm)**


COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A2	4.470	4.570	4.670
A3	2.300	2.350	2.400
b1	0.750	0.800	0.850
b2	1.27 TYPE		
c1	0.450	0.500	0.550
c2	1.250	1.300	1.380
D	9.900	10.000	10.100
D1	10.000TYPE		
D2	8.000TYPE		
E	28.660	28.860	29.060
E1	9.000	9.100	9.200
E2	7.000TYPE		
e	2.540TYPE		
L2	6.350	6.500	6.650
L3	2.50TYPE		
θ1	3° TYPE		
θ2	3° TYPE		
θ3	7° TYPE		
θ4	7° TYPE		